

SANYO	No.2264B	2SB1268/2SD1904
PNP/NPN Epitaxial Planar Silicon Transistors		
High-Current Switching Applications		

Applications

- . Suitable for relay drivers, high-speed inverters, converters, and other general high-current switching applications

Features

- . Suitable for sets whose height is restricted
- . Low collector to emitter saturation voltage

(): 2SB1268

Absolute Maximum Ratings at Ta=25°C

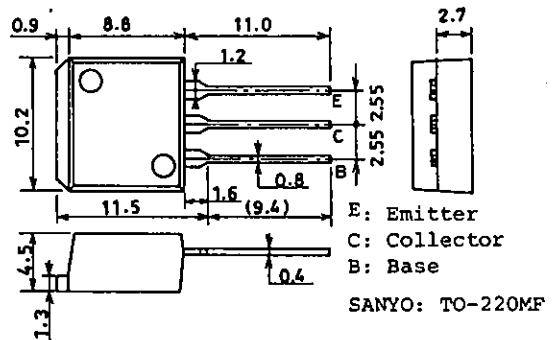
			unit
Collector to Base Voltage	V _{CB0}	(-)60	V
Collector to Emitter Voltage	V _{CEO}	(-)50	V
Emitter to Base Voltage	V _{EBO}	(-)6	V
Collector Current	I _C	(-)5	A
Peak Collector Current	i _{cp}	(-)9	A
Collector Dissipation	P _C	1.65	W
		30	W
	Tc=25°C		
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta=25°C

		min	typ	max	unit
Collector Cutoff Current	I _{CBO} V _{CB} =(-)40V, I _E =0			(-)0.1	mA
Emitter Cutoff Current	I _{EBO} V _{EB} =(-)4V, I _C =0			(-)0.1	mA
DC Current Gain	h _{FE} (1) V _{CE} =(-)2V, I _C =(-)1A	70*		280*	
	h _{FE} (2) V _{CE} =(-)2V, I _C =(-)3A	30			
Gain-Bandwidth Product	f _T V _{CE} =(-)5V, I _C =(-)1A		30		MHz
Output Capacitance	c _{ob} V _{CB} =(-)10V, f=1MHz		100		pF
			(160)		
C-E Saturation Voltage	V _{CE(sat)} I _C =(-)3A, I _B =(-)0.3A			(-)0.4	V
C-B Breakdown Voltage	V _{(BR)CBO} I _C =(-)1mA, I _E =0	(-)60			V
C-E Breakdown Voltage	V _{(BR)CEO} I _C =(-)1mA, R _{BE} =∞	(-)50			V
E-B Breakdown Voltage	V _{(BR)EBO} I _E =(-)1mA, I _C =0	(-)6			V

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Package Dimensions 2049B
(unit: mm)



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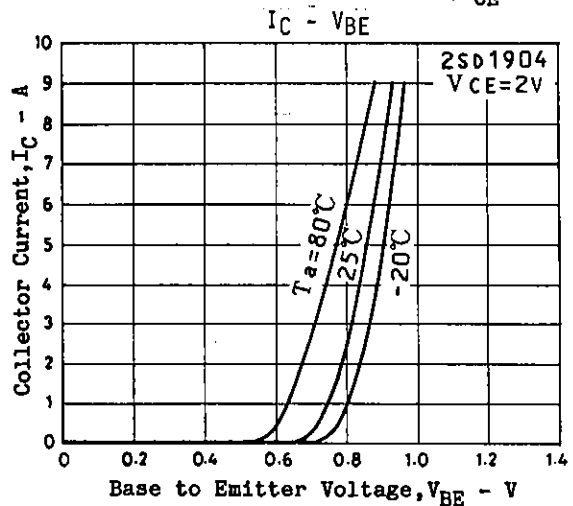
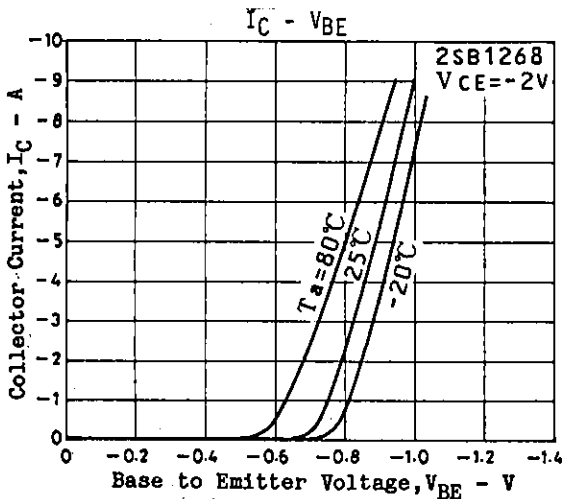
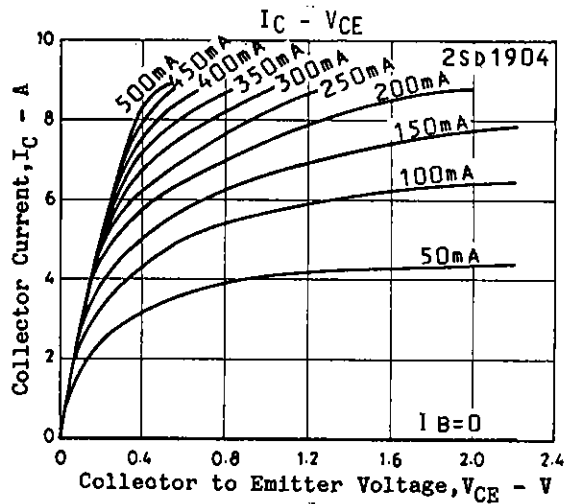
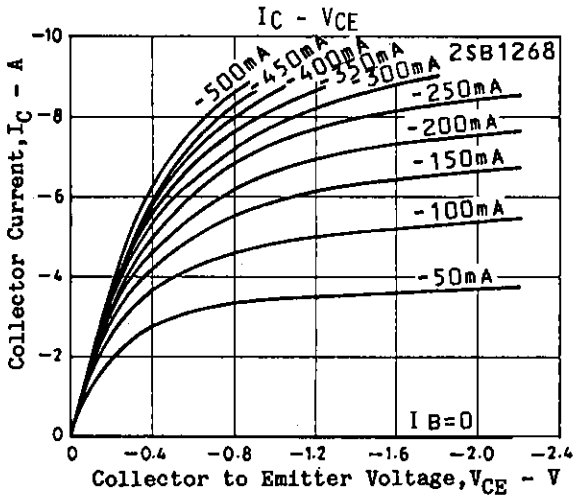
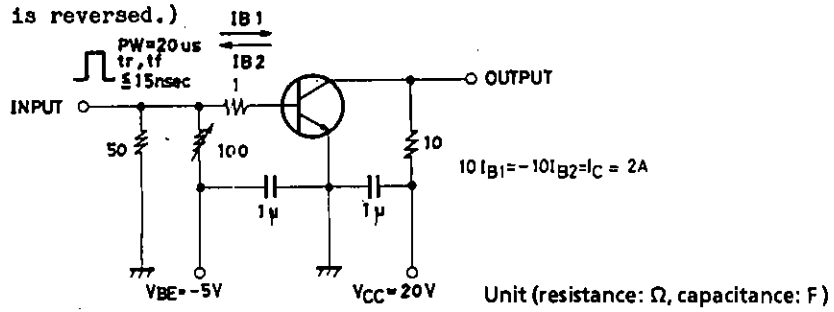
			min	typ	max	unit
Turn-on Time	t_{on}	See specified Test Circuit.		0.1		μs
Storage Time	t_{stg}	"	(0.7)	1.4		μs
Fall Time	t_f	"		0.2		μs

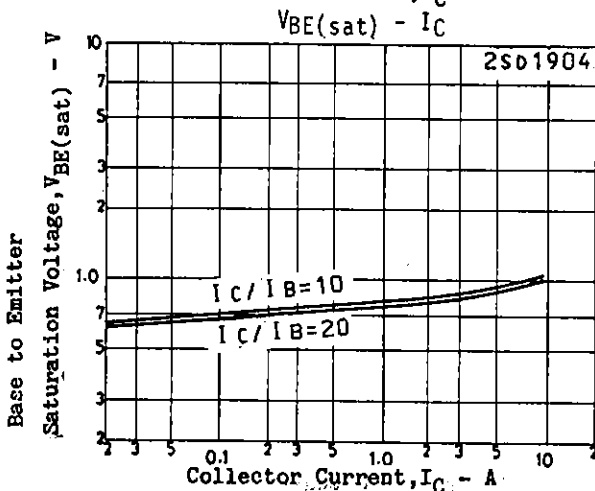
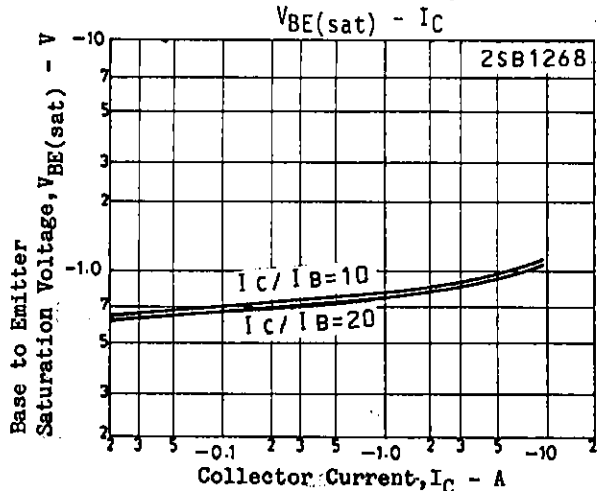
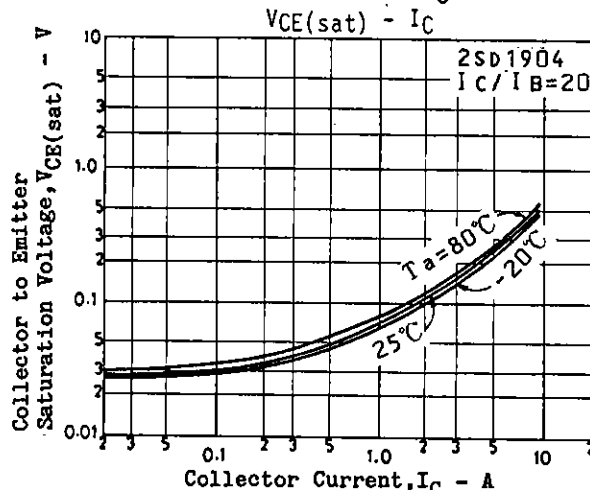
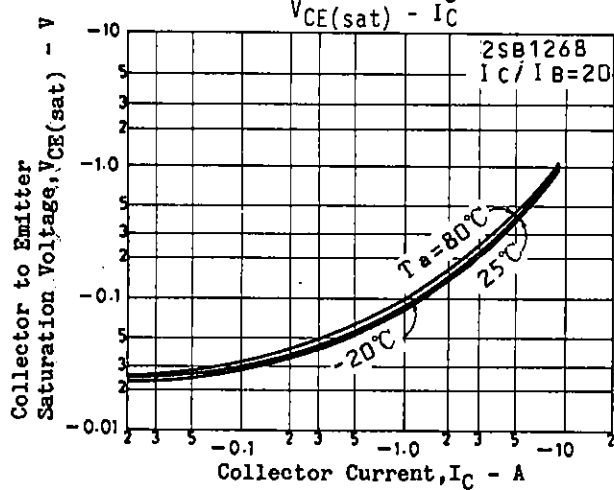
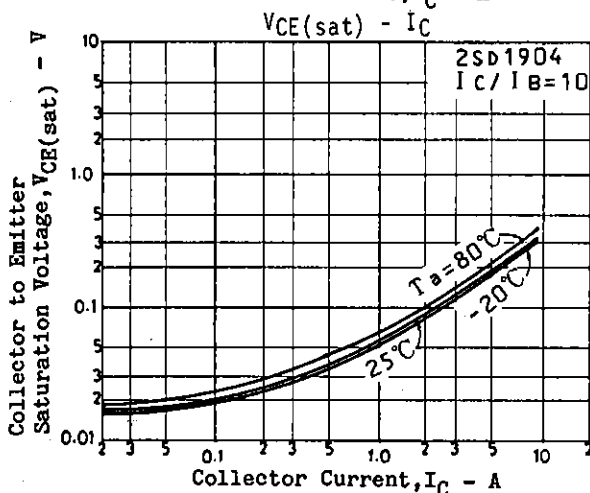
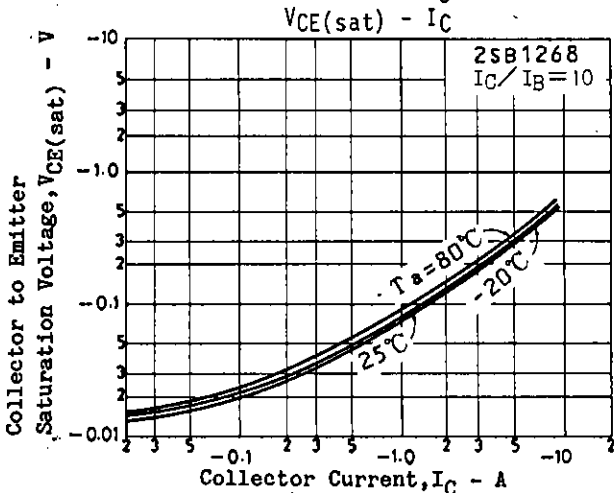
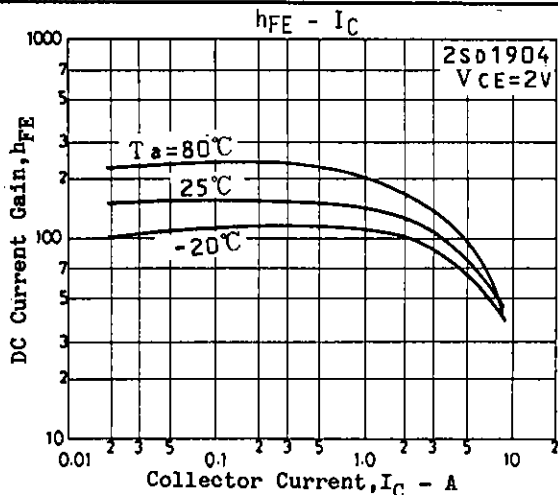
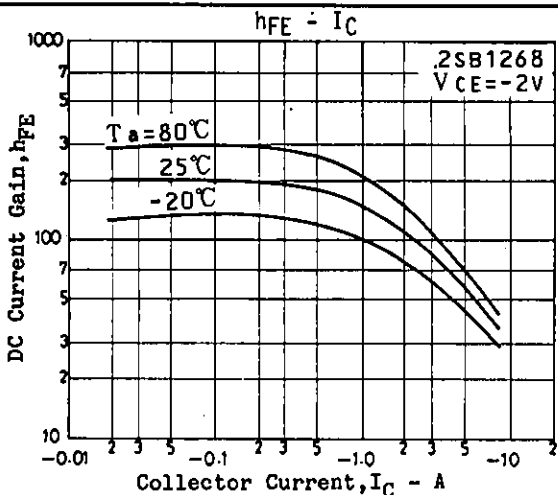
*: The 2SB1268/2SD1904 are classified by 1A h_{FE} as follows:

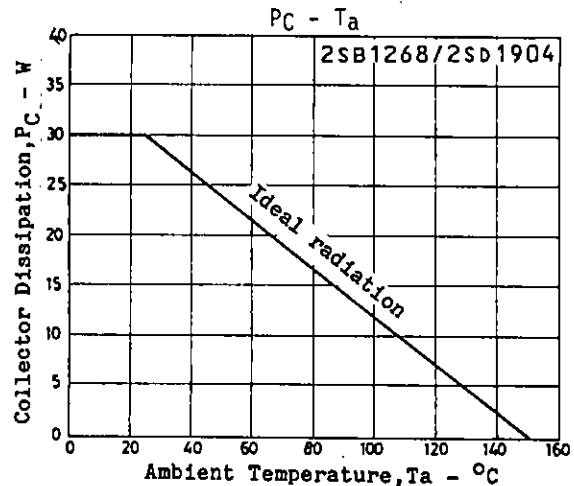
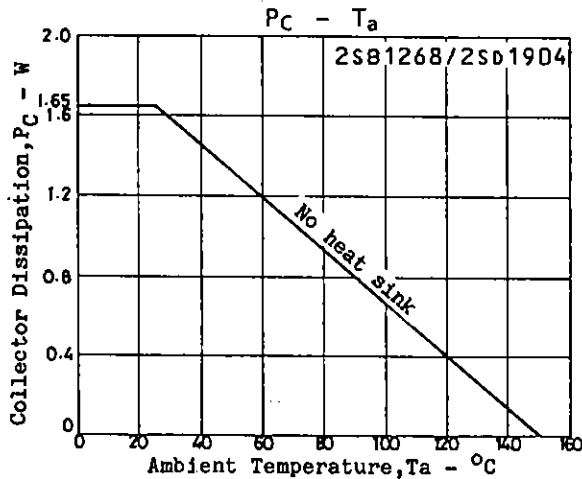
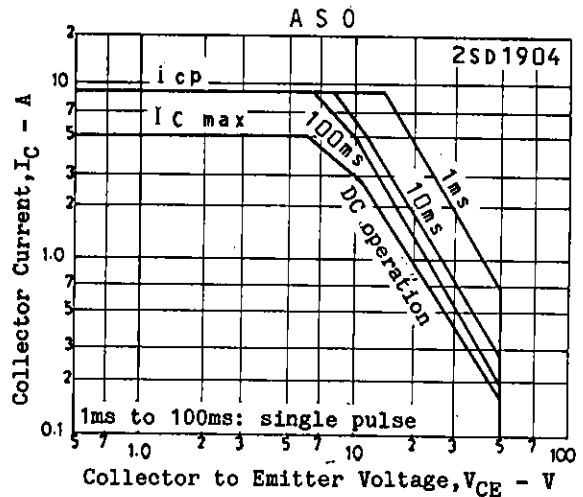
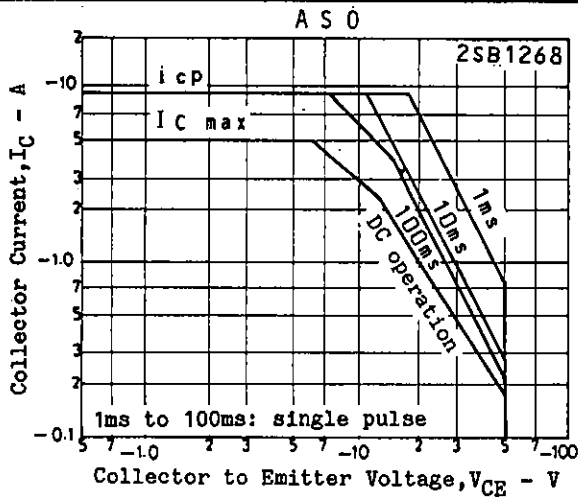
70	Q	140	100	R	200	140	S	280
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Switching Time Test Circuit

(For PNP, the polarity is reversed.)







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